



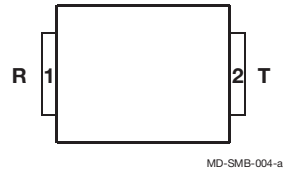
**LOW CAPACITANCE  
BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS**

**TISP4CxxxH3BJ Overvoltage Protector Series**

- Ion-Implanted Breakdown Region**
- Precise and Stable Voltage
  - Low Voltage Overshoot under Surge
  - Low Off-State Capacitance

Device Name	V <sub>DRM</sub> V	V <sub>(BO)</sub> V
TISP4C115H3BJ †	90	115
TISP4C125H3BJ †	100	125
TISP4C145H3BJ †	120	145
TISP4C165H3BJ	135	165
TISP4C180H3BJ †	145	180
TISP4C220H3BJ †	180	220
TISP4C250H3BJ †	190	250
TISP4C290H3BJ †	220	290
TISP4C350H3BJ †	275	350

**SMB Package (Top View)**



**Device Symbol**



**Rated for International Surge Wave Shapes**

Wave Shape	Standard	I <sub>PPSM</sub> A
2/10	GR-1089-CORE	500
10/160	TIA-968-A	200
10/700	ITU-T K.20/21/45	150
10/560	TIA-968-A	100
10/1000	GR-1089-CORE	100

 ..... **UL Recognized Component**

**Description**

This device is designed to limit overvoltages on the telephone line. Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. A single device provides 2-point protection and is typically used for the protection of 2-wire telecommunication equipment (e.g. between the Ring and Tip wires for telephones and modems). Combinations of devices can be used for multi-point protection (e.g. 3-point protection between Ring, Tip and Ground).

The protector consists of a symmetrical voltage-triggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The high crowbar holding current helps prevent d.c. latchup as the diverted current subsides.

Please contact your Bourns representative if the protection voltage you require is not listed.

**How to Order**

Device	Package	Carrier	Order As	Marking Code	Std. Qty.
TISP4CxxxH3BJ	SMB	Embossed Tape Reeled	TISP4CxxxH3BJR-S	4CxxxH	3000

Insert xxx corresponding to device name.

SEPTEMBER 2004 – REVISED JANUARY 2010  
 \*RoHS Directive 2002/95/EC Jan 27 2003 including Annex.  
 Specifications are subject to change without notice.  
 Customers should verify actual device performance in their specific applications.

# TISP4CxxxH3BJ Overvoltage Protector Series

# BOURNS®

## Absolute Maximum Ratings, $T_A = 25\text{ }^\circ\text{C}$ (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
Repetitive peak off-state voltage	$V_{\text{DRM}}$	'4C115H3BJ	±90
		'4C125H3BJ	±100
		'4C145H3BJ	±120
		'4C165H3BJ	±135
		'4C180H3BJ	±145
		'4C220H3BJ	±180
		'4C250H3BJ	±190
		'4C290H3BJ	±220
Non-repetitive peak impulse current (see Notes 1 and 2) 2/10 $\mu\text{s}$ (GR-1089-CORE, 2/10 $\mu\text{s}$ voltage wave shape) 10/160 $\mu\text{s}$ (TIA-968-A, 10/160 $\mu\text{s}$ voltage wave shape) 5/310 $\mu\text{s}$ (ITU-T K.44, 10/700 $\mu\text{s}$ voltage wave shape used in K.20/21/45) 10/560 $\mu\text{s}$ (TIA-968-A, 10/560 $\mu\text{s}$ voltage wave shape) 10/1000 $\mu\text{s}$ (GR-1089-CORE, 10/1000 $\mu\text{s}$ voltage wave shape)	$I_{\text{PPSM}}$		±500
			±200
			±150
			±100
			±100
Non-repetitive peak on-state current (see Notes 1, 2 and 3) 20 ms, 50 Hz (full sine wave) 1000 s, 50 Hz	$I_{\text{TSM}}$		30
			2.1
Junction temperature	$T_J$	-40 to +150	$^\circ\text{C}$
Storage temperature range	$T_{\text{stg}}$	-65 to +150	$^\circ\text{C}$

- NOTES: 1. Initially the device must be in thermal equilibrium with  $T_J = 25\text{ }^\circ\text{C}$ .  
 2. The surge may be repeated after the device returns to its initial conditions.  
 3. EIA/JESD51-2 environment and EIA/JESD51-3 PCB with standard footprint dimensions connected with 5 A rated printed wiring track widths.

## Electrical Characteristics, $T_A = 25\text{ }^\circ\text{C}$ (Unless Otherwise Noted)

Parameter	Test Conditions	Min	Typ	Max	Unit
$I_{\text{DRM}}$ Repetitive peak off-state current	$V_D = V_{\text{DRM}}$ $T_A = 25\text{ }^\circ\text{C}$ $T_A = 85\text{ }^\circ\text{C}$			±5 ±10	$\mu\text{A}$
$V_{(\text{BO})}$ Breakover voltage	$dv/dt = \pm 250\text{ V/ms}$ , $R_{\text{SOURCE}} = 300\ \Omega$			±115 ±125 ±145 ±165 ±180 ±220 ±250 ±290 ±350	V
$V_{(\text{BO})}$ Impulse breakover voltage	$dv/dt \leq \pm 1000\text{ V}/\mu\text{s}$ , Linear voltage ramp, Maximum ramp value = ±500 V $di/dt = \pm 10\text{ A}/\mu\text{s}$ , Linear current ramp, Maximum ramp value = ±10 A			±125 ±135 ±155 ±175 ±190 ±230 ±260 ±300 ±360	V
$I_{(\text{BO})}$ Breakover current	$dv/dt = \pm 250\text{ V/ms}$ , $R_{\text{SOURCE}} = 300\ \Omega$			±600	mA
$V_T$ On-state voltage	$I_T = \pm 5\text{ A}$ , $t_w = 100\ \mu\text{s}$			±3	V
$I_H$ Holding current	$I_T = \pm 5\text{ A}$ , $di/dt = \pm 30\text{ mA/ms}$	±150		±600	mA
$C_O$ Off-state capacitance	$f = 1\text{ MHz}$ , $V_d = 1\text{ V rms}$ , $V_D = -2\text{ V}$	'4C115H3BJ		50	pF
		'4C125H3BJ			
		'4C145H3BJ		45	
		'4C165H3BJ			
		'4C180H3BJ			
		'4C220H3BJ			
			40		

# TISP4CxxxH3BJ Overvoltage Protector Series

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## Thermal Characteristics, $T_A = 25\text{ }^\circ\text{C}$ (Unless Otherwise Noted)

Parameter	Test Conditions	Min	Typ	Max	Unit
$R_{\theta JA}$ Junction to ambient thermal resistance	EIA/JESD51-3 PCB, $I_T = I_{TSM(1000)}$ (see Note 4)			113	$^\circ\text{C/W}$
	265 mm x 210 mm populated line card, 4-layer PCB, $I_T = I_{TSM(1000)}$		50		

NOTE: 4. EIA/JESD51-2 environment and PCB has standard footprint dimensions connected with 5 A rated printed wiring track widths.

## Parameter Measurement Information

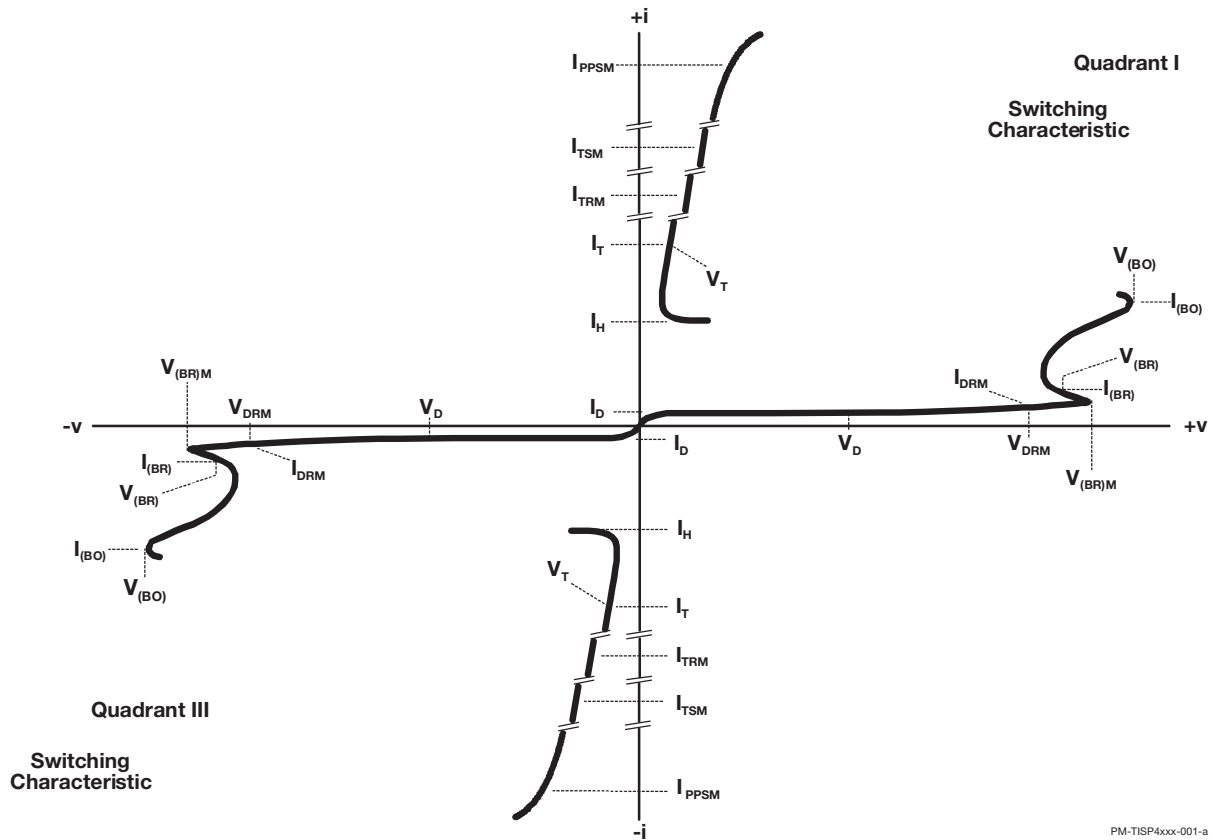
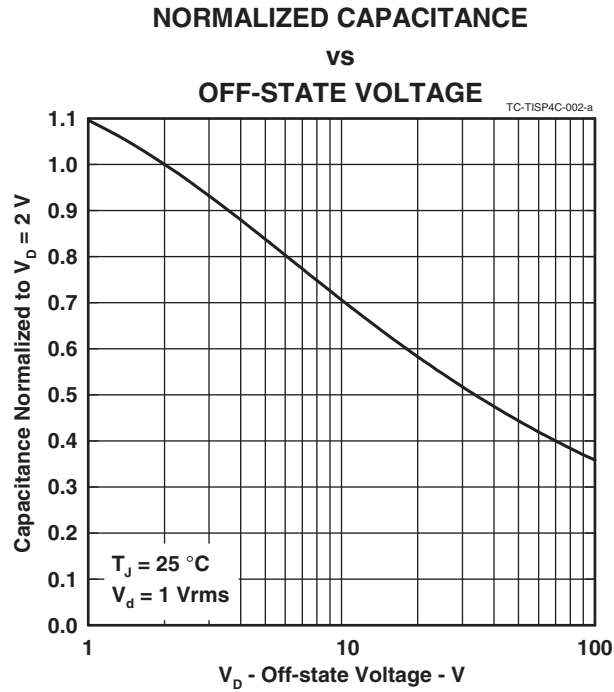


Figure 1. Voltage-Current Characteristic for T and R Terminals  
All Measurements are Referenced to the R Terminal

PM-TISP4xxx-001-a

## Typical Characteristics



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